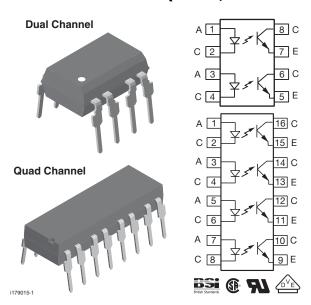


Optocoupler, Phototransistor Output, (Dual, Quad Channel), 110 °C Rated



DESCRIPTION

The ILD1615, ILQ1615 are multi-channel 110 $^{\circ}$ C rated phototransistor optocouplers that use GaAs IRLED emiters and high gain NPN phototransistors. These devices are constructed using over/under leadframe optical coupling and double molded insulation technology resulting a withstand test voltage of 7500 $V_{AC\ PEAK}$ and a working voltage of 1700 V_{RMS} .

The binned min./max. and linear CTR characteristics make these devices well suited for DC or AC voltage detection. Eliminating the phototransistor base connection provides added electrical noise immunity from the transients found in many industrial control environments.

Because of guaranteed maximum non-saturated and saturated switching characteristics, the ILD1615, ILQ1615 can be used in medium speed data I/O and control systems. The binned min./max. CTR specification allow easy worst case interface calculations for both level detection and switching applications. Interfacing with a CMOS logic is enhanced by the guaranteed CTR at $I_{\text{F}} = 1.0$ mA.

FEATURES

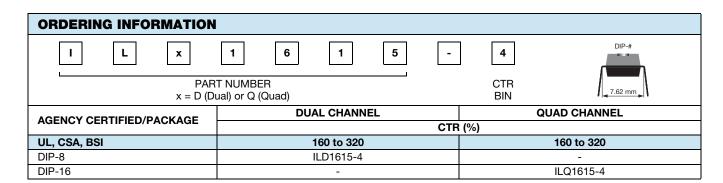
Operating temperature from
- 55 °C to + 110 °C



- · Identical channel to channel footprint
- Dual and quad packages feature:
 - Reduced board space
 - Lower pin and parts count
 - Better channel to channel CTR match
 - Improved common mode rejection
- Isolation test voltage, 5300 V_{RMS}
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

AGENCY APPROVALS

- UL1577, file no. E52744 system code H, double protection
- CSA 93751
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending



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ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT					
INPUT									
Peak reverse voltage		V_{R}	6.0	V					
Forward current		I _F	60	mA					
Surge current		I _{FSM}	1.5	Α					
Power dissipation		P_{diss}	100	mW					
Derate linearly from 25 °C			1.0	mW/°C					
OUTPUT									
Collector emitter breakdown voltage		BV _{CEO}	70	V					
Emitter collector breakdown voltage		BV _{ECO}	7.0	V					
Collector current		I _C	50	mA					
Collector current	t < 1.0 ms	I _C	100	mA					
Power dissipation		P_{diss}	150	mW					
Derate linearly from 25 °C			1.5	mW/°C					
COUPLER									
Storage temperature		T _{stg}	- 55 to + 150	°C					
Operating temperature		T _{amb}	- 55 to + 110	°C					
Soldering temperature (1)	2.0 mm distance from case bottom	T_{sld}	260	°C					
Package power dissipation ILD1615			400	mW					
Derate linearly from 25 °C			5.33	mW/°C					
Package power dissipation ILQ1615			500	mW					
Derate linearly from 25 °C			6.67	mW/°C					
Isolation test voltage	t = 1.0 s	V _{ISO}	5300	V _{RMS}					
Creepage distance			≥ 7.0	mm					
Clearance distance			≥ 7.0	mm					
Isolation resistance	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	≥ 10 ¹²	Ω					
isolation resistance	$V_{IO} = 500 \text{ V}, T_{amb} = 100 ^{\circ}\text{C}$	R _{IO}	≥ 10 ¹¹	Ω					

Notes

⁽¹⁾ Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
INPUT									
Forward voltage	$I_F = 10 \text{ mA}$	V_{F}	1.0	1.15	1.3	V			
Breakdown voltage	$I_R = 10 \mu A$	V_{BR}	6.0	30		V			
Reverse current	V _R = 6.0 V	I _R		0.01	10	μA			
Capacitance	V _R = 0 V, f = 1.0 MHz	Co		25		pF			
OUTPUT									
Collector emitter capacitance	$V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	C _{CE}		6.8		pF			
Collector emitter leakage current	V _{CE} = 10 V	I _{CEO}		5.0	100	nA			
Collector emitter breakdown voltage	$I_{CE} = 0.5 \text{ mA}$	BV _{CEO}	70			V			
Emitter collector breakdown voltage	I _E = 0.1 mA	BV _{ECO}	7.0			V			
PACKAGE TRANSFER CHARACTERISTICS									
Channel/channel CTR match	$I_F = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	CTRX/CTRY	1 to 1		2 to 1				
COUPLER									
Capacitance (input to output)	V _{IO} = 0 V, f = 1.0 MHz	C _{IO}		0.8		pF			
Insulation resistance	V _{IO} = 500 V, T _A = 25 °C	Rs	10 ¹²	10 ¹⁴		Ω			
Channel to channel isolation			500			V_{AC}			

Note

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

Minimum and maximum values are tested requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.





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CURRENT TRANSFER RATIO (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Current transfer ratio (collector emitter saturated)	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	ILD1615-4	CTR _{or} .		100		%	
		ILQ1615-4					%0	
Current transfer ratio (collector emitter)	I 10 m 1 1/ 5 0 1/	ILD1615-4	OTD	160	200	000	%	
	$I_F = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILQ1615-4	CTR _{CE}	160	200	320	90	
	$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-4	CTR _{CE}	56	90		%	
		ILQ1615-4					70	

SWITCHING CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
NON-SATURATED							
Turn-on time	$I_{F} = 10 \text{ mA, } V_{CC} = 5.0 \text{ V, R}_{L} = 75 \Omega,$ $50 \% \text{ of } V_{PP}$		t _{on}		3.0		μs
Rise time	$I_{F} = 10 \text{ mA, } V_{CC} = 5.0 \text{ V, R}_{L} = 75 \ \Omega, \\ 50 \ \% \text{ of V}_{PP}$		t _r		2.0		μs
Turn-off time	$I_{F} = 10 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_{L} = 75 \ \Omega, \\ 50 \ \% \text{ of } V_{PP}$		t _{off}		2.3		μs
Fall time	$I_{F} = 10 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_{L} = 75 \ \Omega, \\ 50 \ \% \text{ of } V_{PP}$		t _f		2.0		μs
Propagation H to L	$I_{F} = 10 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_{L} = 75 \ \Omega, \\ 50 \ \% \text{ of } V_{PP}$		t _{PHL}		1.1		μs
Propagation L to H	$I_{F} = 10 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_{L} = 75 \ \Omega, \\ 50 \ \% \text{ of } V_{PP}$		t _{PLH}		2.5		μs
SATURATED							
Turn-on time	$I_F = 5.0 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_L = 1.0 \text{ k}\Omega, \\ V_{HT} = 1.5 \text{ V}$		t _{on}		6.0		μs
Rise time	I_F = 5.0 mA, V_{CC} = 5.0 V, R_L = 1.0 k Ω , V_{HT} = 1.5 V		t _r		4.6		μs
Turn-off time	I_F = 5.0 mA, V_{CC} = 5.0 V, R_L = 1.0 k Ω , V_{HT} = 1.5 V		t _{off}		25		μs
Fall time	$I_F = 5.0 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_L = 1.0 \text{ k}\Omega, \\ V_{HT} = 1.5 \text{ V}$		t _f		15		μs
Propagation H to L	$I_F = 5.0 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_L = 1.0 \text{ k}\Omega, \\ V_{HT} = 1.5 \text{ V}$		t _{PHL}		5.4		μs
Propagation L to H	$I_F = 5.0 \text{ mA}, \ V_{CC} = 5.0 \text{ V}, \ R_L = 1.0 \text{ k}\Omega, \\ V_{HT} = 1.5 \text{ V}$		t _{PLH}		7.4		μs

COMMON MODE TRANSIENT IMMUNITY (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Common mode rejection output high	$V_{CM} = 50 V_{P-P}, R_L = 1.0 k\Omega, I_F = 0 mA$	CM _H		5000		V/µs	
Common mode rejection output low	$V_{CM} = 50 \ V_{P-P}, \ R_L = 1.0 \ k\Omega, \ I_F = 10 \ mA$	CML		5000		V/µs	
Common mode coupling capacitance		C _{CM}		0.01		pF	

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TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

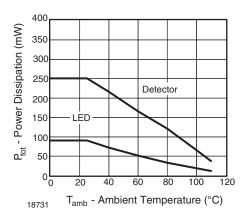


Fig. 1 - Permissible Power Dissipation vs. **Temperature Non-Saturation Operation**

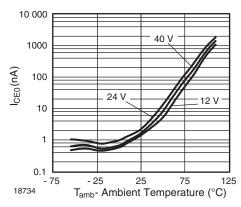


Fig. 4 - Collector to Emitter Dark Current vs. Ambient Temperature

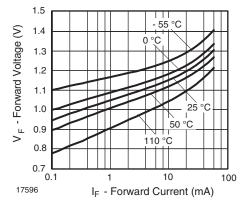


Fig. 2 - Forward Voltage vs. Forward Current

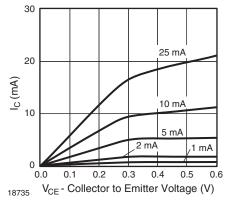


Fig. 5 - Normalized Current vs. Collector Emitter Saturation Voltage

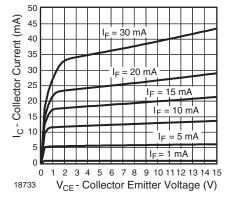


Fig. 3 - Collector Current vs. Collector Emitter Voltage

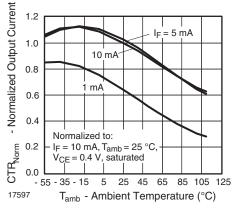


Fig. 6 - Normalized Current Transfer Ratio vs. Ambient Temperature



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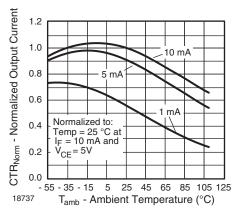


Fig. 7 - Normalized CTR vs. Temperature

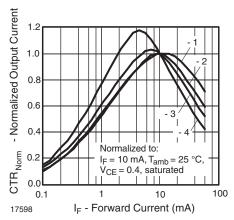


Fig. 8 - Normalized CTR vs. Forward Current

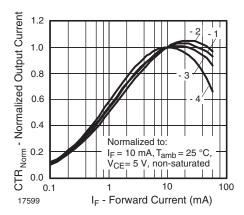


Fig. 9 - Normalized CTR vs. Forward Current

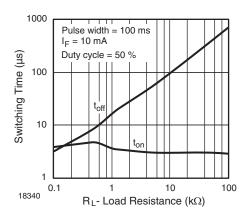


Fig. 10 - Forward Resistance vs. Forward Current

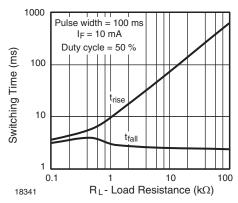
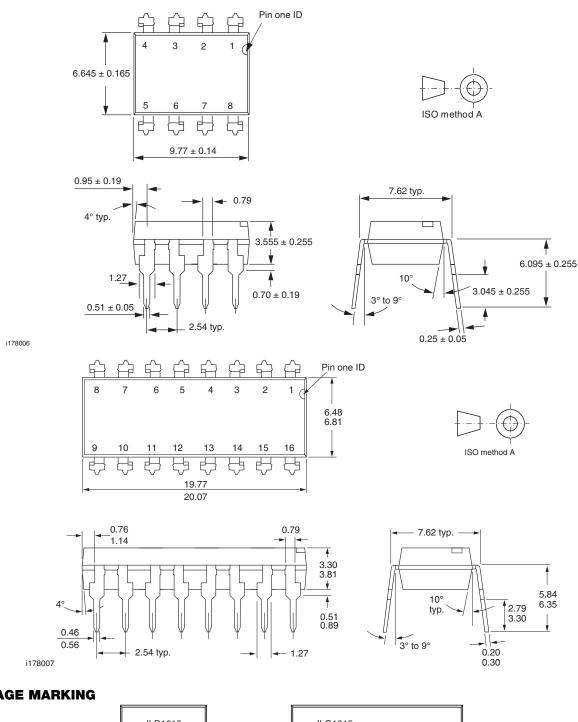


Fig. 11 - Forward Resistance vs. Forward Current

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PACKAGE DIMENSIONS in millimeters



PACKAGE MARKING







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